

In re Patent Application of:
CROCE ET AL.
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TABLE 2

region	Dopant	Thickness [μm]	Doping [Atoms cm^{-3}]
n-body (conductivity "N")	phosphorous	0.25-0.75	5×10^{17} - 5×10^{18}
body-buffer (conductivity "P")	boron	0.15-0.45 below junction with n- body	5×10^{16} - 5×10^{17}
drain well region (conductivity "P")	boron	1.5-4.5 below junction with body- buffer	2.5×10^{15} - 2.5×10^{16}

In the Claims:

Please amend Claims 5 and 14 as follows:

5. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising:

a semiconductor substrate;

a drain region of a first conductivity type adjacent said semiconductor substrate and comprising a superficial buffer region being more heavily doped than adjacent portions of said drain region;

a body region surrounded by said buffer region and having a second conductivity type; and

a source region in said body region and having the first conductivity type.

14. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising: